

Amendments to the Specification

Please amend the third paragraph in page 10, as below:

A gold (Au) or copper (Cu) seed layer 35 is now deposited over the barrier layer 34 by sputtering or electroplating to cover the barrier layer as shown in the figures. The seed layer has a thickness of between about 900 and 1100 Angstroms. The substrate is coated with resist which is exposed and developed by a photolithography process, leaving openings where the metal body is to be formed. Now, the Au or Cu metal body 36 is electroplated on the seed layer 35 to a thickness of between about 2  $\mu\text{m}$  and 20  $\mu\text{m}$ . The resist is removed by an etching process. The barrier/adhesion layer is etched in a self-aligned etch. The barrier/adhesion layer covered by the Au or Cu metal body 36 remains while the barrier/adhesion layer elsewhere is etched away.